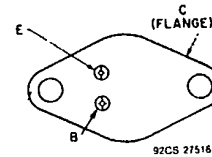


File Number 1109

**BD550, BD550B**

**Silicon Transistors for  
Quasi-Complementary-  
Symmetry Audio Amplifiers**

TERMINAL DESIGNATIONS



JEDEC TO-204AA

The RCA-BD550 and BD550B are silicon n-p-n transistors especially suitable for applications in audio-amplifier circuits, in which they may be used as either driver or output unit.

The devices, together with a variety of other transistors that serve as input devices,  $V_{BE}$  amplifiers for biasing, current sources, load-line limiters (for overload protection), and pre-drivers, may be used to develop several hundred watts of audio output power in quasi-complementary-symmetry audio amplifier configurations that employ parallel output transistors.

The BD-550-series is supplied in the JEDEC TO-204AA hermetic steel case.

MAXIMUM RATINGS, Absolute-Maximum Values:

	BD550	BD550B	
$V_{CBO}$ .....	130	275	V
$V_{CEO}$ .....	110	250	V
$V_{CER}(R_{BE} = 100 \Omega)$ .....	130	275	V
$V_{EBO}$ .....	5		V
$I_C$ .....	7		A
$I_B$ .....	2		A
$P_T$			
At $T_C \leq 25^\circ C$ .....	150		W
At $T_C > 25^\circ C$ .....	See Fig. 1		W/ $^\circ C$
$T_{sig}, T_J$ .....	-65 to 200		$^\circ C$
$T_L$			
At distances $\geq 1/32$ in. (0.8 mm) from seating plane for 10 s max. ....	230		$^\circ C$

3875081 G E SOLID STATE  
Pro Electron Power Transistors

01E 17553 D T-33-13

**BD550, BD550B**

ELECTRICAL CHARACTERISTICS, At Case Temperature ( $T_C$ ) = 25°C

CHARACTERISTIC	TEST CONDITIONS	LIMITS				UNITS
		BD550		BD550B*		
		Min.	Max.	Min.	Max.	
$I_{CER}$ $R_{BE} = 100 \Omega$	$V_{CE} = 110 V$ $V_{CE} = 250 V$	—	1	—	—	mA
$I_{CEO}$	$V_{CE} = 95 V$ $V_{CE} = 200 V$	—	5	—	5	mA
$I_{EBO}$	$V_{EB} = 5 V$	—	1	—	1	mA
$V_{CEO}$	$I_C = 0.2 A$	110	—	250	—	V
$V_{CER}$	$I_C = 0.2 A; R_{BE} = 100 \Omega$	130	—	275	—	V
$f_T$	$I_C = 0.2 A; V_{CE} = 10 V$	5 typ.		5 typ.		MHz
$h_{FE}$	$I_C = 4 A; V_{CE} = 4 V$ $I_C = 2 A; V_{CE} = 4 V$	15	75	—	—	
$V_{CE(sat)}$	$I_C = 4 A; I_B = 0.5 A$ $I_C = 2 A; I_B = 0.25 A$	—	2	—	2	V
$V_{BE}$	$I_C = 4 A; V_{CE} = 4 V$ $I_C = 2 A; V_{CE} = 4 V$	0.75	1.75	—	—	V
$I_{S/D}$	$V_{CE} = 80 V; t = 1 S$ $V_{CE} = 140 V; t = 1 S$	1.87	—	—	—	A

▲For characteristics curves and test conditions, refer to published data for prototype RCA8638D (File 1060).

\*For characteristics curves and test conditions, refer to published data for prototype 2N5240 (File 321).

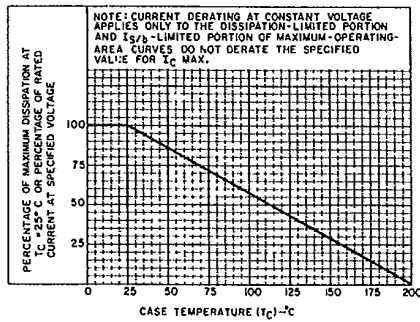


Fig. 1 — Derating curve for all types.

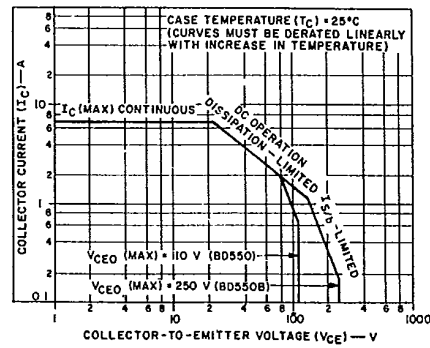


Fig. 2 — Maximum operating areas for all types.